



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Min-Lung HUANG et al. Confirmation No: 8687
Appl. No. : 10/820,855
Filed : April 9, 2004
Title : Under Bump Metallization Structure Of A Semiconductor Wafer

TC/A.U. : 2814
Examiner : A. Kalam

Docket No.: : HUAN3262/REF
Customer No: : 23364

REQUEST FOR RECONSIDERATION AFTER FINAL REJECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of August 27, 2007. The period for responding to the outstanding Official Action has been extended to expire on December 27, 2007 by the filing herewith of a Petition for a One Month Extension of Time and payment of the required fees.

The §103 Rejection of Claims 1-4, 6 and 7

The rejection of claims 1-4, 6 and 7 under 35 U.S.C. §103(a) as being unpatentable over Applicant's Admitted Prior Art (AAPA) in view of Andricacos et al. (US Pat. No. 6,224,690) has been carefully considered but is most respectfully traversed in light of the following comments.

The Official Action urges that AAPA (paragraphs [0004] and [0005] and Figure 1 of the instant application) discloses an under bump metallization as recited in claim 1, including an under bump metallization layer comprising an adhesive layer, a first barrier layer, and a wetting layer, but expressly acknowledges that AAPA fails to disclose a second barrier layer disposed on the wetting layer wherein the material of the second barrier layer comprises tin and nickel.